Takashi Hanada

List of Publications by Year
in descending order

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154 papers	2,897 citations	172457 29 h-index	214800 47 g-index
156 all docs	156 docs citations	156 times ranked	2325 citing authors

#	Article	IF	Citations
1	Origin of forward leakage current in GaN-based light-emitting devices. Applied Physics Letters, 2006, 89, 132117.	3.3	148
2	Structure and electronic state of the TiO2 and SrO terminated SrTiO3(100) surfaces. Surface Science, 1993, 287-288, 377-381.	1.9	140
3	Band alignment at a ZnO/GaN (0001) heterointerface. Applied Physics Letters, 2001, 78, 3349-3351.	3.3	125
4	Structural variation of cubic and hexagonal MgxZn1âˆ’xO layers grown on MgO(111)âˆ•c-sapphire. Journal of Applied Physics, 2005, 98, 054911.	2.5	107
5	Control of crystal polarity in a wurtzite crystal:â€ƒZnO films grown by plasma-assisted molecular-beam epitaxy on GaN. Physical Review B, 2002, 65, .	3.2	100
6	Surface structures ofGaAs{111}A,Bâˆ’(2Ã—2). Physical Review B, 2001, 64, .	3.2	81
7	Rocking-curve analysis of reflection high-energy electron diffraction from the Si(111)-(â√3 Ã— â√3)R30Â°-Al, -Ga, and -In surfaces. Physical Review B, 1995, 51, 13320-13325.	3.2	72
8	Growth of GaN single crystals from a Naâ€“Ga melt at 750Â°C and 5MPa of N2. Journal of Crystal Growth, 2000, 218, 7-12.	1.5	68
9	Control of polarity of ZnO films grown by plasma-assisted molecular-beam epitaxy: Zn- and O-polar ZnO films on Ga-polar GaN templates. Applied Physics Letters, 2000, 77, 3571-3573.	3.3	63
10	Atomic structure of theGaAs(001)âˆ’(2Ã—4)surface under As flux. Physical Review B, 2002, 65, .	3.2	60
11	Molecular beam epitaxy of Bi2Sr2CuOx and Bi2Sr2Ca0.85Sr0.15Cu2Ox ultra thin films at 300Â°C. Journal of Crystal Growth, 1991, 112, 745-752.	1.5	58
12	Low stacking-fault density in ZnSe epilayers directly grown on epi-ready GaAs substrates without GaAs buffer layers. Applied Physics Letters, 2001, 78, 165-167.	3.3	55
13	Study of the Si(111)7 Ã— 7 surface by RHEED rocking curve analysis. Surface Science, 1994, 313, 143-154.	1.9	53
14	Anisotropic shape of self-assembled InAs quantum dots: Refraction effect on spot shape of reflection high-energy electron diffraction. Physical Review B, 2001, 64, .	3.2	50
15	Lattice relaxation mechanism of ZnO thin films grown on c-Al2O3 substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2007, 91, .	3.3	50
16	Molecular Beam Epitaxy Study of Bi2Sr2CuOxUsing NO2as an Oxidizing Agent. Japanese Journal of Applied Physics, 1990, 29, L1111-L1113.	1.5	49
17	Red to blue wavelength emission of N-polar $(000ar{1})$ InGaN light-emitting diodes grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2015, 8, 061005.	2.4	49
18	Surface structure of SrTiO3(001) with various surface treatments. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2649-2654.	2.1	48

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19	Electron-trap centers in ZnO layers grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 032909.	3.3	45
20	Polarity control of ZnO films on (0001) Al2O3 by Cr-compound intermediate layers. Applied Physics Letters, 2007, 90, 201907.	3.3	45
21	Study of successive phase transitions of the Si(001)-Bi surface by RHEED. Surface Science, 1991, 242, 137-142.	1.9	44
22	Lattice strain in bulk GaN epilayers grown on CrN/sapphire template. Applied Physics Letters, 2009, 94, 082105.	3.3	41
23	Characteristics of Schottky contacts to ZnO:N layers grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 042110.	3.3	39
24	Two-step MBE growth of ZnO layers on electron beam exposed (111)CaF2. Journal of Crystal Growth, 1999, 207, 87-94.	1.5	37
25	ZnTe-Based Light-Emitting-Diodes Grown on ZnTe Substrates by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 229, 995-999.	1.5	37
26	Structure and composition of the ZnSe(001) surface during atomic-layer epitaxy. Physical Review B, 1999, 60, 8326-8332.	3.2	35
27	Comparative study of photoluminescences for Zn-polar and O-polar faces of single-crystalline ZnO bulks. Applied Physics Letters, 2008, 93, .	3.3	32
28	Surface reactions at the controlled structure of SrTiO3(001). Surface and Interface Analysis, 1994, 22, 412-416.	1.8	31
29	Evolution of initial layers of plasma-assisted MBE grown ZnO on (0001)GaN/sapphire. Journal of Crystal Growth, 2000, 214-215, 81-86.	1.5	30
30	Control and characterization of ZnO/GaN heterointerfaces in plasma-assisted MBE-grown ZnO films on GaN/Al2O3. Applied Surface Science, 2000, 159-160, 441-448.	6.1	30
31	ZnO epilayers on GaN templates: Polarity control and valence-band offset. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1429.	1.6	28
32	Effects of interfacial layer structures on crystal structural properties of ZnO films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 90-96.	2.1	26
33	Structure and magnetic properties of Cr-doped GaN. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1308.	1.6	25
34	Impact of V/III ratio on electrical properties of GaN thick films grown by hydride vapor-phase epitaxy. Applied Physics Letters, 2007, 91, .	3.3	25
35	The reaction of copper and calcium dipivaloylmethanates (Cu(DPM)2 and Ca(DPM)2) with hydroxyls on oxide surface. Surface Science, 1991, 242, 508-512.	1.9	23
36	Structural characteristics and magnetic properties of Î»-MnO2 films grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2001, 90, 351-354.	2.5	23

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37	Optimization of ZnSe growth on miscut GaAs substrates by molecular beam epitaxy. Journal of Crystal Growth, 2003, 249, 128-143.	1.5	23
38	Novel Method for Site-Controlled Surface Nanodot Fabrication by Ion Beam Synthesis. Nano Letters, 2005, 5, 771-776.	9.1	23
39	Capacitance-voltage characteristics of ZnOâˆ•GaN heterostructures. Applied Physics Letters, 2005, 87, 162104.	3.3	23
40	Atomic layer control in Srâ€Cuâ€O artificial lattice growth. Applied Physics Letters, 1994, 65, 1717-1719.	3.3	22
41	Strain-free GaN thick films grown on single crystalline ZnO buffer layer with in situ lift-off technique. Applied Physics Letters, 2007, 90, 061907.	3.3	22
42	Improvement of surface morphology of nitrogen-polar GaN by introducing indium surfactant during MOVPE growth. Japanese Journal of Applied Physics, 2014, 53, 085501.	1.5	22
43	Control of polarity of heteroepitaxial ZnO films by interface engineering. Applied Surface Science, 2002, 190, 491-497.	6.1	21
44	Ga-polar GaN film grown by MOVPE on cleaved ScAlMgO₄(0001) substrate with millimeter-scale wide terraces. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600754.	1.8	21
45	Effects of a low-temperature buffer layer on structural properties of ZnO epilayers grown on (111)CaF2 by two-step MBE. Journal of Crystal Growth, 2000, 208, 389-394.	1.5	20
46	Improvement in crystallinity of ZnSe by inserting a low-temperature buffer layer between the ZnSe epilayer and the GaAs substrate. Journal of Crystal Growth, 2002, 242, 95-103.	1.5	20
47	Real-time analysis of adsorption processes of Zn on theGaAs(001)â^'(2Ã—4)surface. Physical Review B, 1999, 60, 8713-8718.	3.2	18
48	Structural characteristic and magnetic properties of Mn oxide films grown by plasma-assisted MBE. Journal of Crystal Growth, 2001, 227-228, 955-959.	1.5	18
49	Hybridization of Cr3dâ€“N2pâ€“Ga4sin the wide band-gap diluted magnetic semiconductorGa1â^'xCrxN. Physical Review B, 2004, 70, .	3.2	18
50	Study of surface structure by kinetic-energy dependence of polar-angle photoelectron diffraction. Surface Science, 1989, 221, 244-252.	1.9	17
51	Surface structure and oxidation of Si(001)Bi. Vacuum, 1990, 41, 650-651.	3.5	17
52	Layer controlled growth of oxide superconductors. Applied Surface Science, 1994, 82-83, 487-493.	6.1	17
53	Structure of Se-adsorbed GaAs(111)A-(23Ã—23)-R30Â° surface. Physical Review B, 1999, 59, 8032-8036.	3.2	17
54	Strain Relaxation of Self-Assembled InAs/GaAs(001) Quantum Dots Observed by Reflection High-Energy Electron Diffraction. Japanese Journal of Applied Physics, 2001, 40, 1878-1881.	1.5	16

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55	Photoresponsivity of ZnO Schottky barrier diodes. Journal of Vacuum Science & Technology B, 2006, 24, 1595.	1.3	16
56	Enhancement of surface migration by Mg doping in the metalorganic vapor phase epitaxy of N-polar GaN/sapphire. Japanese Journal of Applied Physics, 2014, 53, 05FL05.	1.5	16
57	Surface reconstruction and crystal structure of MgSe films grown on ZnTe substrates by MBE. Journal of Crystal Growth, 2000, 208, 253-258.	1.5	15
58	Growth and characterization of Ga1â^'xCrxN with high Cr content grown on ZnO templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2869-2873.	0.8	15
59	Electrical properties of ZnO/GaN heterostructures and photoresponsivity of ZnO layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 946-951.	0.8	15
60	Molecular beam epitaxial growth of superconducting Ba2DyCu3O6.5thin films at 420â€‰Â°C using NO2as an oxidant. Applied Physics Letters, 1992, 61, 1971-1973.	3.3	14
61	Molecular Beam Epitaxy of Al Doped n-ZnSe. Physica Status Solidi (B): Basic Research, 2002, 229, 381-384.	1.5	14
62	Growth of Polarity-Controlled ZnO Films on (0001) Al2O3. Journal of Electronic Materials, 2008, 37, 736-742.	2.2	14
63	Ultrathin film of Bi2Sr2CuOx formed by molecular beam epitaxy using NO2. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 4104-4105.	2.1	13
64	Glancing Angle Dependence of the X-Ray Emission Measured under Total Reflection Angle X-Ray Spectroscopy (TRAXS) Condition during Reflection High Energy Electron Diffraction Observation. Japanese Journal of Applied Physics, 1992, 31, L1503-L1505.	1.5	13
65	Electron Standing Wave at a Surface during Reflection High Energy Electron Diffraction and Adatom Height Determination. Physical Review Letters, 1995, 75, 669-672.	7.8	13
66	Effect of lattice mismatch on surface morphology of InAs quantum dots on (100) In1â^'xAlxAs/InP. Applied Physics Letters, 2001, 79, 4331-4333.	3.3	13
67	Homogeneity improvement of N-polar $(000ar{1})$ InGaN/GaN multiple quantum wells by usingc-plane sapphire substrate with off-cut-angle towarda-sapphire plane. Japanese Journal of Applied Physics, 2016, 55, 05FA09.	1.5	13
68	Characterization of the ScAlMgO4 cleaving layer by X-ray crystal truncation rod scattering. Journal of Applied Physics, 2018, 123, .	2.5	13
69	Characterization of N-doped ZnO layers grown on (0001) GaN/Al2O3 substrates by molecular beam epitaxy. Current Applied Physics, 2004, 4, 625-629.	2.4	12
70	Strain relaxation mechanism of InGaN thin film grown on m â€GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 444-446.	0.8	12
71	New Models for the 7 Ã—7, 5 Ã—5, 2 Ã—8 Structures on Si(111) and Ge(111) Surfaces. Journal of the Physical Society of Japan, 1984, 53, 1911-1914.	1.6	11
72	Self-assembled formation of ZnCdSe quantum dots on atomically smooth ZnSe surfaces on GaAs(001) by molecular beam epitaxy. Thin Solid Films, 1999, 357, 1-7.	1.8	11

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73	Adsorption of Zn on the GaAs(001)-(2Ã—4) surface. Applied Physics Letters, 1999, 74, 2975-2977.	3.3	10
74	The high quality ZnO growth on c-Al2O3 substrate with Cr2O3 buffer layer using plasma-assisted molecular beam epitaxy. Applied Surface Science, 2008, 254, 7786-7789.	6.1	10
75	Phase diagram on phase purity of InN grown pressurizedâ€reactor MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 654-657.	0.8	10
76	X-ray photoelectron spectroscopy study on the CrN surface grown on sapphire substrate to control the polarity of ZnO by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2009, 255, 8582-8586.	6.1	9
77	Reaction between copper dipivaloylmethanate Cu(DPM)2 and H2O adsorbed on SrTiO3(100). Surface Science, 1992, 262, L139-L143.	1.9	8
78	In situobservation of strain-induced optical anisotropy ofZnSxSe1â^'x/GaAs(110)during molecular-beam epitaxy. Physical Review B, 1999, 60, 8909-8914.	3.2	8
79	Self-organized formation processes of CdSe quantum dots studied by reflection high-energy electron diffraction. Journal of Crystal Growth, 2000, 214-215, 703-706.	1.5	8
80	Experimental demonstration of Fano-type resonance in photoluminescence of ZnS:Mnâ•SiO2 one-dimensional photonic crystals. Applied Physics Letters, 2005, 87, 171106.	3.3	8
81	Growth and scintillation properties of Tl-doped CsI/CsCl/NaCl ternary eutectic scintillators. Japanese Journal of Applied Physics, 2021, 60, SBBK01.	1.5	8
82	Growth and scintillation properties of Ce doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e270" altimg="si3.svg"><mml:msup><mml:mrow /><mml:mrow><mml:mn>6</mml:mn></mml:mrow></mml:msup></mml:math>LiBr/LaBr<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e278" altimg="si13.svg"><mml:msub><mml:mrow	1.6	8
83	Atomic layer epitaxy processes of ZnSe on GaAs (001) as observed by beam-rocking reflection high-energy electron diffraction (RHEED) and total-reflection-angle X-ray spectroscopy (TRAXS). Journal of Crystal Growth, 1999, 201-202, 490-493.	1.5	7
84	Observation of bulk Bragg-reflection using reflection high-energy electron diffraction on Mn3O4-like films grown on MgO (001) by molecular beam epitaxy. Surface Science, 2000, 445, 151-158.	1.9	7
85	Formation processes of CdTe quantum dots on ZnTe substrates studied by reflection high-energy electron diffraction and photoluminescence. Journal of Applied Physics, 2002, 92, 5490-5493.	2.5	7
86	Deep-level-transient spectroscopy of heavily Al-doped ZnSe layers grown by molecular-beam epitaxy. Journal of Applied Physics, 2004, 96, 7332-7337.	2.5	7
87	Surface structure of InGaAs/InP(0â€‰0â€‰1) ordered alloy during and after growth. Applied Surface Science, 2004, 237, 230-234.	6.1	7
88	Observation of a filled electronic state in the conduction band of InN. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1846-1849.	0.8	7
89	Structural investigation of nitrided c-sapphire substrate by grazing incidence x-ray diffraction and transmission electron microscopy. Applied Physics Letters, 2007, 91, 202116.	3.3	7
90	Effect ofc-plane sapphire substrate miscut angle on indium content of MOVPE-grown N-polar InGaN. Japanese Journal of Applied Physics, 2014, 53, 05FL07.	1.5	7

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91	Development of Data-Analysis Software for Total-Reflection High-Energy Positron Diffraction (TRHEPD). Acta Physica Polonica A, 2020, 137, 188-192.	0.5	7
92	In situ measurement of carrier concentration in n-ZnSe by reflectance difference spectroscopy (RDS). Journal of Crystal Growth, 2000, 214-215, 547-551.	1.5	6
93	Determination of carrier concentration in n-ZnSe by reflectance difference spectroscopy: Experimental results and model calculation. Journal of Applied Physics, 2002, 92, 139-143.	2.5	6
94	X-ray diffraction characterization of MBE grown Pr1â^'xSrxMnO3 thin films on NGO(1 1 0). Applied Surface Science, 2002, 190, 408-415.	6.1	6
95	Characteristics of deep levels in Al-doped ZnSe grown by molecular beam epitaxy. Materials Science in Semiconductor Processing, 2003, 6, 567-571.	4.0	6
96	High-energy photoemission spectroscopy of ferromagnetic Ga1â^'xMnxN. Materials Science in Semiconductor Processing, 2003, 6, 503-506.	4.0	6
97	Analysis of the relation between leakage current and dislocations in GaN-based light-emitting devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 37-40.	0.8	6
98	Suppression of metastable-phase inclusion in N-polar (0001Â¯) InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 106, .	3.3	6
99	Crystal growth of La2Hf2O7 by micro-pulling-down method using W crucible. Journal of Crystal Growth, 2022, 583, 126547.	1.5	6
100	Structure and growth mechanism of ultrathin films of Bi cuprates grown by low-temperature MBE. Physica C: Superconductivity and Its Applications, 1991, 190, 27-30.	1.2	5
101	Polarity control of GaN grown on pulsed-laser-deposited AlN/GaN template by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FA04.	1.5	5
102	Crystal growth and scintillation properties of tube shape-controlled Ce-doped Y₃Al₅O₁₂ single crystals grown by micro-pulling-down method. Applied Physics Express, 2020, 13, 125503.	2.4	5
103	Large size growth of terbium doped BaCl2/NaCl/KCl eutectic for radiation imaging. Japanese Journal of Applied Physics, 0, , .	1.5	5
104	sim-trhepd-rheed â€“ Open-source simulator of total-reflection high-energy positron diffraction (TRHEPD) and reflection high-energy electron diffraction (RHEED). Computer Physics Communications, 2022, 277, 108371.	7.5	5
105	Scanning tunneling microscopy study of the initial reaction of SiH2Cl2 molecules with the Si(111)-7Ã—7 surface. Applied Surface Science, 1998, 130-132, 23-28.	6.1	4
106	Formation and evolution of strain-induced self-assembled dot. Microelectronics Journal, 2005, 36, 216-218.	2.0	4
107	Electrical characterization for ZnO layers grown on GaN templates by molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1281.	1.6	4
108	Correlation between ZnO Nanowire Growth and the Surface of AlN Substrate. Crystal Growth and Design, 2006, 6, 2640-2642.	3.0	4

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109	Molecular beam epitaxy and magnetic properties of GaMnNAs. Journal of Crystal Growth, 2007, 301-302, 642-646.	1.5	4
110	An empirical equation including the strain effect for optical transition energy of strained and fully relaxed GaN films. Journal Physics D: Applied Physics, 2010, 43, 175101.	2.8	4
111	Thermodynamic model for metalorganic vapor-phase epitaxy of N-polar group-III nitrides in step-flow growth mode: Hydrogen, competitive adsorption, and configuration entropy. Physical Review Materials, 2019, 3, .	2.4	4
112	Dependence of the V/III Ratio on Indium Incorporation in InGaN Films Grown by Metalorganic Vapour Phase Epitaxy. Journal of Nanoscience and Nanotechnology, 2020, 20, 2979-2986.	0.9	4
113	Realization of one-chip-multiple-wavelength laser diodes with IIâ€“VI/IIIâ€“V compound semiconductors. Applied Physics Letters, 2003, 82, 4095-4097.	3.3	3
114	GaN nanodot fabrication by implant source growth. Microelectronics Journal, 2005, 36, 456-459.	2.0	3
115	Soft X-ray spectroscopy of diluted magnetic semiconductor Ga1âˆ’xMxN (Mâ€‰=â€‰Cr, Mn). Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 707-710.	1.7	3
116	Slowdown in development of self-assembled InAsâˆ•GaAs(001) dots near the critical thickness. Journal of Vacuum Science & Technology B, 2006, 24, 1886.	1.3	3
117	The effect of hydrogen irradiation and annealing on the low-temperature growth of homoepitaxial ZnO layers grown on (0001) ZnO substrates by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2008, 254, 3120-3124.	6.1	3
118	Tilted Domain and Indium Content of InGaN Layer on m-Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 04DH01.	1.5	3
119	Investigation of indium incorporation into InGaN by nitridation of sapphire substrate in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 417-420.	0.8	3
120	Growth and scintillation properties of Tl-doped CsI/KI/KCl ternary eutectics. Journal of Crystal Growth, 2021, 573, 126287.	1.5	3
121	Tilted Domain and Indium Content of InGaN Layer onm-Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 04DH01.	1.5	3
122	Temperature Characteristics of Resonance Frequency for Double-Layered Thickness-Shear Resonator. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 870-877.	3.0	3
123	Growth of Tb-doped BaCl2/NaCl/KCl ternary eutectic and its luminescence properties. Journal of Crystal Growth, 2022, 580, 126467.	1.5	3
124	Properties of self-organized CdSe quantum dots on an atomically flat (111)A ZnSe surface. Applied Surface Science, 1998, 130-132, 755-759.	6.1	2
125	Adsorption processes of Se on the GaAs(111)Aâ€“(2x2) surface. Applied Surface Science, 2000, 162-163, 419-424.	6.1	2
126	Growth of PrSrMnO3-like thin films on NGO (110) substrates by plasma assisted MBE. Journal of Crystal Growth, 2001, 227-228, 960-965.	1.5	2

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127	Correlation of surface chemistry of GaAs substrates with growth mode and stacking fault density in ZnSe epilayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1948.	2.1	2
128	Measurements of a component of the piezo-optic tensor of Si by reflectance difference spectroscopy. Journal of Applied Physics, 2003, 94, 1458-1460.	2.5	2
129	Electronic structure of the Ga1â^'xCrxN studied by high-energy photoemission spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 561-564.	1.7	2
130	Ordering of In and Ga in Epitaxially Grown In_{0.53}Ga_{0.47}As Films on (001) InP Substrates. Materials Transactions, 2006, 47, 1115-1120.	1.2	2
131	Crystal growth of La2Zr2O7 by micro-pulling-down method using Mo and W crucibles. Journal of Crystal Growth, 2021, 575, 126357.	1.5	2
132	Selective surface reaction between metal compounds and surface functional groups. Physica C: Superconductivity and Its Applications, 1991, 190, 148-150.	1.2	1
133	Measurements of the Linear Electro-Optic Coefficients of ZnTe by RDS. Physica Status Solidi (B): Basic Research, 2002, 229, 605-609.	1.5	1
134	MBE growth and characterization of A-site deficient, low-field magnetoresistance (Pr1â^'xSrx)yMnO3â^'Î´ oriented thin films. Journal of Crystal Growth, 2003, 251, 619-622.	1.5	1
135	Optical anisotropy of GaNAs grown on GaAs(001) substrate. Current Applied Physics, 2004, 4, 640-642.	2.4	1
136	Crystal Growth. , 2007, , 329-445.		1
137	Structural characterization of MgO/c-Al2O3 interfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1715-1718.	0.8	1
138	Characterization of free-standing GaN substrates prepared by self lift-off. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2617-2620.	0.8	1
139	Metal catalyst enhanced growth of high quality and density GaN dots on Si(111) by implant source growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2314-2317.	0.8	1
140	Study of local segregation in GaInNAs using EXAFS measurements. Journal of Physics and Chemistry of Solids, 2008, 69, 298-301.	4.0	1
141	Optical properties and electrical properties of heavily Al-doped ZnSe layers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 259-264.	2.1	1
142	Atomic Layer Growth of SrCuO2 Thin Film by Molecular Beam Epitaxy.. Hyomen Kagaku, 1993, 14, 283-287.	0.0	1
143	Growth and scintillation properties of directionally solidified Ce:LaCl3/AECl2 (AEâ€¯=â€¯Mg, Ca, Sr) eutectic Scintillators. Journal of Crystal Growth, 2022, 584, 126549.	1.5	1
144	Study on the Elementary Steps of the Epitaxial Growth of Bi-Sr-Ca-Cu-O on the Surface of Si and Mgo by Means of Rheed and Photoelectron Spectroscopies.. Materials Research Society Symposia Proceedings, 1989, 169, 715.	0.1	0

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145	In situ RHEED and XPS studies on ceramic layer epitaxy in UHV system. AIP Conference Proceedings, 1991, , .	0.4	0
146	Ultra thin film of Bi cuprate grown by a low temperature molecular beam epitaxy. Physica C: Superconductivity and Its Applications, 1991, 185-189, 2057-2058.	1.2	0
147	Optical anisotropy and surface morphology of InGaAs lattice-mismatched with GaAs(001). Current Applied Physics, 2004, 4, 621-624.	2.4	0
148	GaNAs(001) surface phases under growing condition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1341.	1.6	0
149	Low-Temperature Growth of A1N thin films on ZnO templates prepared on Ak<inf>2</inf>O<inf>3</inf> substrates. , 2006, , .		0
150	Magnetic and Crystalline properties of GaMnNAs and Low-temperature annealing effect. , 2006, , .		0
151	Effect of anion-to-cation supplying ratio on the surface morphology of AlN films grown on ZnO substrates at low temperature. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 61-64.	2.1	0
152	Electrochemical isothermal-capacitance-transient spectroscopy: A new depth profiling method of deep levels. Review of Scientific Instruments, 2011, 82, 093905.	1.3	0
153	Effect of Nitridation on Indium-Composition of InGaN Films. Key Engineering Materials, 2012, 508, 193-198.	0.4	0
154	Effect of Sapphire Nitridation and Group-III Source Flow Rate Ratio on In-Incorporation Into InGaN Grown by Metalorganic Vapor Phase Epitaxy. Journal of Nanoscience and Nanotechnology, 2014, 14, 6112-6115.	0.9	0